The Defects Genome of Janus Transition Metal Dichalcogenides

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Abstract

Two-dimensional (2D) Janus Transition Metal Dichalcogenides (TMDs) have attracted much interest due to their exciting quantum properties arising from their unique two-faced structure, broken-mirror symmetry, and consequent colossal polarisation field within the monolayer. While efforts have been made to achieve high-quality Janus monolayers, the existing methods rely on highly energetic processes that introduce unwanted grain-boundary and point defects with still unexplored effects on the material's structural and excitonic properties Through High-resolution scanning transmission electron microscopy (HRSTEM), density functional theory (DFT), and optical spectroscopy measurements; this work introduces the most encountered and energetically stable point defects. It establishes their impact on the material's optical properties. HRSTEM studies show that the most energetically stable point defects are single (V_S and V_{Se}) and double chalcogen vacancy ($V_S - V_{Se}$), interstitial defects (M_i), and metal impurities (M_W) and establish their structural characteristics. DFT further establishes their formation energies and related localized bands within the forbidden band. Cryogenic excitonic studies on h-BN-encapsulated Janus monolayers offer a clear correlation between these structural defects and observed emission features, which closely align with the results of the theory. The overall results introduce the defect genome of Janus TMDs as an essential guideline for assessing their structural quality and device properties.

Introduction

Named after the Roman god, Janus transition metal dichalcogenides (TMDs) are a novel class of atomically thin two-dimensional (2D) materials¹. Unlike classical TMDs² with the chemical formula MX_2 (M=Mo, W and X=chalcogens), Janus TMDs are characterized by the 'broken' mirror symmetry, resulting from top and bottom surfaces containing different chalcogen atoms. As such, they can be referred to in M_X^Y notation to indicate the bottom chalcogen atom type with the subscript X and the top chalcogen atom type as Y

superscript^{3,4}. Theoretical and experimental studies to date have shown that the broken mirror symmetry along with permanent dipole lends Janus TMDs with exotic effects such as Rashbatronics⁵⁻⁷, colossal piezoelectricity^{8,9}, long-lived dipolar excitons¹⁰, enhanced Dzyaloshinskii-Moriya Interaction¹¹, skyrmion formation^{12,13}, and polarisation driven photocatalytic water splitting¹⁴.

So far, much effort has focused on synthesizing 2D Janus materials with high structural, electronic, and excitonic quality, creating strain-engineered high-order structures such as Janus nanoscrolls reported recently ^{15,16}, as well as finding effective ways to expand the library of 2D Janus materials¹⁷⁻²⁰. These studies readily opened routes for exploring complex many-body physics in these materials systems^{10,21-27}. Despite efforts to realize structurally perfect Janus layers, the existing methods still involve either plasma or pulsed laser processing to transform classical TMDs into 2D Janus layers^{3,4,18-20,28}. These non-equilibrium and highly energetic processes introduce unintentional point and grain boundary (GB) defects. However, the relationship between the material's structural characteristics and intrinsic electronic and optical responses remains underexplored²⁹⁻³¹. For example, understanding the behaviour of defects in 2D materials³²⁻⁴¹ has enabled the realization of many quantum effects, including valley coherence⁴²⁻⁴⁶, spin polarised Landau levels^{47,48}, valley Zeeman effect⁴⁹, ferromagnetic ordering^{50,51}, the realization of single quantum emitters⁵²⁻⁵⁴. Similarly, the fundamental understanding of the effects of defects on the structural and material properties of Janus TMDs holds the key to their high-quality manufacturing, understanding their quantum properties, and assessing device properties of 2D Janus TMDs.^{15,55-58}

Here, our work introduces the first comprehensive investigation of impurities and defects in Janus monolayers²⁸ and correlates them to their excitonic properties. Employing ultra-low electron dose HR-STEM on Janus W_{Se}^{S} and Mo_{Se}^{S} monolayers, we identify and structurally characterize the most common point defects and grain boundaries. Using Density Functional Theory (DFT), the results establish the defect formation energy and identify the most thermodynamically favourable defect states. Cryogenic photoluminescence spectroscopy of hBN encapsulated Janus TMDs enabled us to identify three isolated bound exciton emission lines and correlate these spectral signatures to point defects ^{36,59,60,61}. Overall results, interpreted DFT simulations, correlate imperfections to the optical properties of 2D Janus TMDs.

Results

2D Janus synthesis was carried out using established growth techniques in the literature, starting from large area chemical vapour deposited (CVD)^{15,17,21,28} WSe₂ and MoSe₂ or exfoliated sheets from CVT grown vdW crystals^{15,28,33}. These classical monolayers were transformed into Janus TMDs using plasma-based techniques ^{15,17,28} at high excitonic qualities. More specifically, classical TMDs were positioned in a custom-designed quartz chamber, retrofitted with a viewing window that couples it into Raman and PL spectrometers for in-situ monitoring capabilities to ensure high-quality Janus layer synthesis. The conversion process was monitored in real time by analyzing the intensity and full-width-at-half-maximum (FWHM) of the most prominent Raman peaks for classical TMDs' (A'₁) Raman mode and Janus (A¹₁) modes⁶²⁻⁶⁴. Fig.1a shows the time-dependent Raman spectrum of an exfoliated 1L-WSe₂ during its conversion to Janus W^S_{Se}. The overlaying characteristic E' + A'₁ modes^{62,63} of 1L-WSe₂ at 254 cm⁻¹, shown in the red spectra in Fig. 1a, gradually disappear once the hydrogen plasma is ignited and the top chalcogen layer is etched. This Raman mode gradually broadens, indicating the reduction of crystallinity of 1L-WSe₂ and slowly blue-shifts to a higher frequency with increasing time, showing the strengthening of the partial W-Se bond. Furthermore, at ~ 90 seconds into the reaction, a new Raman mode at ~ 290 cm⁻¹ emerges and

gradually redshifts and increases in intensity, shown by the overlaid spectra (bright orange to salmon pink) in Fig. 1a. between ~90 seconds and ~150 seconds. This mode is attributed to the A_1^1 Raman mode in Janus W_{Se}^{S} ^{10,15,28,64}. Eventually, at time ~150 seconds the E'+ A'_1 modes of 1L-WSe₂ are entirely diminished, and the A_1^1 Raman mode stabilizes at 284 cm⁻¹ frequency. The observed result is consistent with previous reports on 2D Janus conversion and the behaviour of the A_1^1 Raman mode is indicative of the relaxation of the partially etched and stiffened 1L-WSe₂ structure²⁸.

To gain insight into the microscopic structure of Janus monolayers during the Janus conversion process, HR-STEM was performed on a 1L-WSe₂ sample on a Quantifoil TM carbon grid at different stages of the Janus conversion, as shown in Fig. 1b to 1d. High Angle Annular Dark Field (HAADF) images on 1L-WSe₂, before the conversion, clearly shows the hexagonal lattice arrangement of the tungsten atom as bright spots and dimmer spots from two selenium atoms sitting on top of each other (Fig. 1b)^{10,28}. The Rutherford scattering intensity from the tungsten and selenium atomic columns is plotted in the top panel of Fig. 1e (blue spectra) for the region shown by the blue line in Fig. 1b, where the arrow shows the direction from which the line profile in Fig. 1e is plotted.



Figure 1: Conversion of 1L-WSe₂ to Janus W_{Se}^{S} - (a) Contour plot of time-dependent Raman spectra on 1L-WSe₂ to Janus W_{Se}^{S} : The red line overlay shows the $E' + A'_1$ Raman mode from 1L-WSe₂. The white line overlay shows the Janus A_1^1 mode in W_{Se}^{S} (b-d) HR-STEM on 1L-WSe₂ at different times of conversions shown in Fig. 1a: (b)) Shows HAADF micrograph of 1L-WSe₂, the structure is representative of the Raman spectra obtained before the ignition of plasma in Fig. 1a. (c) HAADF micrograph of partially converted 1L-WSe₂ to Janus W_{Se}^{S} showing patches of Janus embedded into the parent TMDs, structure representative of the Raman spectra obtained between 60 to 150 seconds in Fig. 1a (d) HAADF micrograph of fully converted Janus W_{Se}^{S} , representative of the Raman spectra obtained at 240 seconds of reaction. (e) Corresponding line profile of the HAADF micrographs in Fig 1b, 1c and 1d: (Blue) Line profile of 1L-WSe₂ shown in Fig. 1b. (Orange) line profile of partially converted Janus + TMDs structure shown in Fig. 1c. (Red) line profile of fully converted Janus W_{Se}^{S} in Fig. 1d.

The Z contrast in Fig.1b, from a single tungsten atom (Z=74), is comparable to two selenium atoms (Z=2*34) and is consistent with previous reports^{15,17,18,28}. To capture the intermediate state of the Janus conversion (between 60 seconds to 150 seconds), the sample is converted for that duration on a Quantifoil grid supported on a Silicon substrate to prevent the bottom chalcogen layer from being etched. Fig. 1c shows the HAADF micrograph of the partially converted 1L-WSe₂ structure, where the conversion process is stopped after ~60 to 150 seconds. The orange curve in the middle panel of Fig. 1e shows the Z-contrast intensity extracted along the orange line in the HAADF micrograph in Fig.~1c. As the replacing chalcogen sulphur (Z=16) is lighter than the parent chalcogen selenium (Z=34), the overall intensity of the Janus chalcogen column decreases when compared with the intensity of the chalcogen column in the parent TMDs^{65,66}. As a result, regions with dimmer spots can be observed in the HAADF micrograph. The sample

is further subjected to the Janus conversion process until reaching the point of complete Janus conversion after ~240 seconds Fig. 1d (red line) shows the characteristic HAADF micrograph of the Janus – W_{Se}^{S} structure, where the intensity of the chalcogen columns is significantly and homogeneously reduced compared to the parent WSe₂²⁸.

The Z-contrast scattering intensity of the transition metal and chalcogen atomic columns for the W_{Se}^S is plotted in the bottom panel of Fig. 1e. The selenium atoms (Z=34) have undergone a complete replacement by the lighter sulphur atoms (Z=16), resulting in the diminishing intensity when compared with the parent TMDs as shown in Fig. 1b. Although Fig. 1d shows a high degree of crystallinity, it is not representative the true crystal quality of the resulting Janus TMDs. This is because, after the conversion process, microscopic regions with a relative abundance of selenium impurities remain in the Janus material ^{10,28}. By comparing the Raman intensity of out-of-plane mode A'₁ of the parent TMDs before and after Janus conversion, one can gauge the conversion efficiency of the Janus conversion process ^{15,28}. All the samples studied in this letter showed above 98.3% conversion efficiency. The total reaction time required to achieve this efficiency was approximately 7 minutes and 30 seconds, including purge and vacuum cycles. This suggests that the etching step in the reaction is swift, as seen from the contour plot in Fig 1a; however, the chalcogen replacement dominates the total conversion time and is the rate-determining step, consistent with the recent study⁶⁷. Additionally, HAADF simulations of monolayer WSe₂ and Janus W^S_{Se} (See SI Fig. S1) are compared with the experimental data in Fig. 1b and 1d, the simulations match with the experimental datasets, and the overall findings from the HAADF micrographs and our Raman spectra indicate the presence of residual chalcogen atoms from the parent TMDs, vacancies, and point defects even within the most crystalline Janus materials ^{10,28}.

Identification of point defects in Janus W_{Se}.

HR-STEM with a large Field of View (FOV) on W_{Se}^S shows the presence of various types of point defects selected from highly defective regions (Fig. 2a). While other sections of the 2D Janus W_{Se}^S do not contain a high density of defects, the selected region in Fig.2a closely captures all the four commonly observed energetically stable defects (total 7) across other fabricated samples. In a typical sample, four main types of point defects have been identified and indicated with circles: single chalcogen vacancies V_S and V_{Se} (red), double chalcogen vacancy $V_S - V_{Se}$ (pink); interstitial defect M_i (light blue) and metal impurity M_w (dark blue) consistent with defects observed for classical TMDs ^{20,35,40,68-70} except $V_S - V_{Se}$ double vacancies.

High magnification HAADF STEM image of single chalcogen vacancy is shown in Fig. 2b. The red arrow indicates the direction of the line profile, which is plotted in Fig. 2f and shown schematically in the right part of that figure. The HAADF STEM intensity provides distinguishable evidence of the absence of the two different chalcogen atoms due to the difference in their atomic number (Z). The top (bottom) panel shows the HAADF STEM intensity of a region with a sulphur (selenium) vacancy. Figure 2c shows the HAADF STEM image of a region with a double chalcogen vacancy (marked by a pink arrow). The line intensity profile is plotted in Fig. 2g and schematically presented in Fig 2g (left). In addition to the chalcogen vacancies, Fig. 2d also shows the presence of interstitial atoms (shown by the bright spot next to the centre of the light blue arrow); the line profile in Fig. 2h depicts the presence of an additional atom on the chalcogen site. Lastly, a bright atom is observed in Fig. 2e and shown within a dark blue arrow. This

point defect is attributed to a metal impurity atom in the tungsten site, as depicted by the higher intensity in the line profile in Fig. 2i and schematically shown to the right.



Figure 2: Identification of point defects in 1L-Janus W_{Se}^{S} - (a) HAADF image of 1L- Janus W_{Se}^{S} , circles show typical defects: single chalcogen vacancy, V_S and V_{Se} (red circle); double chalcogen vacancy, $V_S - V_{Se}$ (pink circle); interstitial defect, M_i (light blue circle) and metal impurity, M_w (dark blue circle) (*scalebar-5Å*). (b) HAADF image of V_S and V_{Se} taken from a region in Fig. 2a. The arrowhead (red) indicates the direction from which the line profile (red) in (f) is constructed. The right part of (f) shows the schematic representation of the HAADF image in Fig. 2b. Similarly, (c) shows the HAADF image, and (g) shows the line profile (pink arrow) together with the schematic representation (right side) for the $V_S - V_{Se}$ (d) shows the HAADF image, and (h) shows Mi's line profile (light blue). Lastly, (e) shows the HAADF image, and (i) shows the corresponding line profile (dark blue) with schematic representation for a M_w

Here, single chalcogen V_{Se} can be associated with defects in parent CVD or exfoliated WSe₂ or the formation of double selenium vacancy during plasma etching followed by sulphur decoration during the conversion process, yielding V_{Se}^{28} . Similarly, the lighter chalcogen vacancy (sulphur) can be attributed to an incomplete or partial replacement process¹⁷. We note that the concentration of the double chalcogen vacancy is significantly smaller than that of the single chalcogen vacancy. This is likely related to the initial crystal quality and the defect activation energy of the double chalcogen vacancy during the Janus process²⁸. Additionally, HAADF STEM simulations on the chalcogen vacancies are shown in SI Fig. S2 and are consistent with the experimental data in Fig. 2b and 2c. In contrast, observed M_i and M_w metal impurities are likely carried from the transition metal oxide or transition metal precursors used during CVD and CVT synthesis, respectively ^{33,71}, and these defects are repeatedly observed in Janus monolayers from exfoliated and CVD-grown samples. Based on our observations, a higher number of single chalcogen vacancies, in particular, V_S is observed and is attributed to the Janus conversion for even the most crystalline sample presently reported in literature ¹⁰, suggesting that even the best-in-class Janus sample has a large abundance of defects^{10,28}.

One-dimensional (1D) defects in CVD Grown Janus Samples:

Unlike Janus TMDs realized from exfoliated classical TMDs, CVD samples exhibit additional onedimensional defects, suggesting an overall lower crystal quality of the parent TMD when compared to exfoliated monolayers ^{68,72,73} as depicted in Fig.3a^{34,74-76}. As an example, the HAADF STEM micrograph of Janus Mo^S_{Se} monolayers in Fig. 3a clearly show 1D line defects and grain boundaries (GBs) in addition to the previously discussed point defects. These 1D defects have been attributed to the polycrystalline nature of the parent CVD thin films^{28,34,68} and elevated synthesis temperature in an uncontrolled reaction environment compared to bulk crystal growth techniques such as CVT and Flux methods ^{68,72,73,76}.

Fig. 3b presents a high magnification region to show an example of a grain boundary in Janus Mo^S_{Se} sample. The red box indicates the line profile, plotted in Fig. 3d, with a line defect schematically shown on the right side. This defect consists of chalcogen sites that have not undergone any etching and retains the parent chalcogen atom. This can be attributed to significantly different bonding characteristics around GBs compared to the single crystal parent TMDs requiring different process parameters (RF power) for their Janus conversion. This observation is consistent with established literature and suggests that precise control over the microstructural kinetics in the GB regions during the conversion process could yield higher conversion efficiency for polycrystalline samples ^{68,73}. Notably, a higher density of defects, commonly found in Janus TMDs converted from CVD samples, might be rearranging themselves to form these 1D defects outlined in Fig.3.

In stark contrast, the behaviour of 2D line defects shown in Fig. 3c is opposite to what is observed for the GBs in Fig 2b. The HAADF STEM and the subsequent line profile (blue box) show that these regions' chalcogen sites are terminated with the replacement chalcogen atom (sulphur). The chalcogen atom sites in the line defect have converted completely, suggesting a lower bond energy in this region compared to the parent matrix and GBs ^{28,34,68}. This indicates that optimizing the Janus conversion process for a higher yield and crystal quality in the case of any CVD sample will likely compromise the power tuning for conversion between these two regions. Ultimately, reducing the overall number of higher-order defects and limiting them to one type will likely contribute the most towards obtaining higher crystal quality in Janus TMDs



Figure 3: Higher order defects in Janus Mo_{Se}^{S} - (a) HAADF image of Janus Mo_{Se}^{S} synthesized from CVD-grown monolayers that show higher-order line and grain boundary defects. (b) HAADF image of GBs (red box) that was observed in Janus Mo_{Se}^{S} , their line profile analysis (d) shows that the chalcogen sites in the line defects are terminated with unetched parent chalcogen atoms, and the right part of (d) shows the schematic representation of the structure observed in Fig. 3b. Similarly, (c) HAADF image of a line defect (blue box) observed in Janus Mo_{Se}^{S} . Unlike the GBs, the chalcogen sites are entirely replaced by sulphur atoms (e) shows the line profile of the line defect in Fig. 3c along with the schematic representation of the crystal structure (right part)

Theoretical Insights into Defect-Property Relations:

First-principles computations with hybrid functional PBE0 were performed to study the thermodynamic stabilities of the relevant defects in Janus W_{Se}^{S} , including simple vacancy V_{S} , V_{Se} , V_{W} , and complex defects $V_{S}-V_{Se}$ and $V_{S}-V_{Se}-V_{W}$, as summarised in Fig 4. We have used a recently proposed scheme ensuring a proper representation of the band edges while enforcing 'Koopman's condition for the defects levels (see methods)⁷⁷. The simulated defect configurations can be found in SI Fig. S3. Fig. 4a shows the defect formation energy versus Fermi level for all the defects in different charge states. It was found that among the simple defects, the chalcogen vacancies have the lowest formation energy, with V_{S} slightly more stable than V_{Se} . All the defects that involve V_{W} show a high formation energies (see SI Fig. S4), as shown in previous studies of metal vacancies in TMDs ⁷⁸⁻⁸⁰. We now turn our attention to the interaction between chalcogen vacancies. Our results show that $V_{S-}V_{Se}$ vacancy complex is slightly more stable compared to non-interacting pairs of simple chalcogen vacancies with a binding energy of around 50 meV, as shown in the inset of Fig. 4a. We further note that the neutral charge state of V_{S} , V_{Se} , and $V_{S-}V_{Se}$ are the most relevant ones as they span the majority energy range in the band gap. With the most relevant defects identified, we plotted the electronic structure of V_{S}^{0} , V_{Se}^{0} and $V_{S-}V_{Se}^{0}^{0}$, as shown in Fig. 4b.



Figure 4: First-principles calculations of defect levels in 1L Janus W_{Se}^{S} – (a) defect formation energy diagram for intrinsic single and complex defects with charge states -1, 0, and +1 (solid lines). Dashed lines indicate the total energy of two single defects that compete with the formation of complex defects. V_S , V_{Se} and $V_S - V_{Se}$ are favourable in a neutral charge state within the bandgap. The inset shows a zoomed-in plot illustrating that forming the complex defect $V_S - V_{Se}$ is slightly more favourable with the presence of V_S and V_{Se} . We use the elemental chemical potential for each atom. (b) Single particle Kohn-Sham energy levels for the three most favourable defects at neutral charge state.

The Kohn-Sham level diagrams show that all three defects have four degenerate defect levels originating from the W dangling bond. We found that the chalcogen defects in Janus share a similar electronic structure compared with WS₂ and WSe₂^{77,81,82}. Further incorporation of spin-orbit coupling (SOC) splits the defect levels by 210, 214, and 293 meV for V_S^0 , V_{Se}^0 and $V_S - V_{Se}^0$, respectively (see SI Fig. S5 for SOC effect). We note that an optical excitation of these defects will involve the excitation of an electron in the valence band to the unoccupied defect state, forming a defect-bound exciton. We approximate the excitation energy based on the Kohn-Sham energy difference between the lowest unoccupied defect level and band edges (ΔKS), which are 1.73 eV, 1.65 eV and 1.59 eV for V_S^0 , V_{Se}^0 and $V_S - V_{Se}^0$, respectively. This computed trend will be used to understand the experimental PL spectrum discussed in the following section.

Correlation of Bound Exciton Emission to Defect States:

Our previous studies showed that significantly brighter emission in CVD Janus samples on SiO₂/Si substrates are related to bound exciton emission instead of previously identified neutral excitons^{10,15,28}. To correlate defect states to emission characteristics, fully encapsulated h-BN/ W_{Se}^{S} / h-BN heterostructures were fabricated to ensure no effective charge transfer takes place between SiO₂ and Janus monolayers and to reduce the exciton linewidth^{60,61}. Fig. 5a shows the optical image of the fabricated Janus/h-BN heterostructure consisting of Janus W_{Se}^{S} sandwiched between two separate few-layer h-BN layers on a silicon substrate with 300 nm thick thermal oxide. Monolayer WSe₂ was exfoliated and deterministically transferred onto the h-BN/SiO₂/Si, followed by Janus conversion to yield W_{Se}^{S} and the Janus monolayer was fully encapsulated by another few-layer h-BN, as depicted in Fig. 5b. The room-temperature PL spectrum from fully encapsulated W_{Se}^{S} (Fig. 5c) reveals a broad emission at 1.55 eV, a shoulder at 1.69 eV, and a distinct peak at 1.84 eV.

We note that the PL emission characteristics show significant differences between encapsulated and not encapsulated W_{Se}^S as shown in Fig. 5c inset. Without encapsulation, W_{Se}^S exhibits a single emission peak at 1.84 eV, attributed to the neutral exciton emission^{10,28}. The prominence of this peak in the non-encapsulated device compared to the encapsulated device can be understood considering the charge transfer between the SiO₂ interface and the Janus TMDs. In the non-encapsulated device at room temperature, the defect levels are occupied due to effective doping from the substrate ^{10,63,83}, which suppresses bound exciton emission. This is schematically shown in Fig. 5d. Upon encapsulation with h-BN, no effective charge transfer can occur, enabling the defect states to participate in exciton recombination pathways and give rise to the bound exciton emission.



Figure 5: Defect characterization of 1L Janus W_{Se}^{S} **encapsulated by h-BN and probed using cryogenic optical spectroscopy - (a)** Optical image of h-BN encapsulated 1L Janus W_{Se}^{S} . (b) Shows the schematic representation of the encapsulated Janus sample. (c) PL spectra of the fully encapsulated Janus monolayer show a substantial defect-related emission (solid red spectra), along with the characteristic neutral exciton emission X^0 at 1.84 eV at room temperature and additional peaks indicated by grey arrows. The cumulative peak fit (dotted line) is shown with its deconvolution, where three additional peaks labelled P1, P2 and P3 are identified (blue lines show their contribution). (inset) depicts a comparison between a non-encapsulated sample on SiO₂ and a fully hBN-encapsulated sample. (d) and (e) show the filling of defect levels associated with the charged transfer from the SiO₂ substrate to the non-encapsulated sample and the presence of unoccupied defect states when the sample is between hBN layers. (f, g and h) shows power-dependent PL spectra at 4K of the three peaks, P1, P2 and P3 identified in spectra (c).

Moreover, we note that the intensity of the defect-related emission bands is significantly more prominent compared to unbound excitons in the hBN-encapsulated Janus W_{Se}^{S} device, suggesting that bound-exciton emission is the dominant path for exciton recombination in this device. The difference in the emission energy and intensity of the bound and neutral excitons in encapsulated and non-encapsulated samples is likely related to the combination of various phenomena, namely, physisorption of Oxygen (O₂) and moisture (H₂O), different effective dielectric screening from h-BN, and strain within the Janus monolayer⁸⁴⁻⁸⁶. In the case of the molecular physisorption process, which can be considered only for non-encapsulated samples, the monolayer Janus TMDs retain the p-type behaviour of the parent WSe₂, where the adsorption from oxygen and moisture depletes the sample from electrons, effectively increasing the trion emission and reducing the neutral exciton emission ^{84,86}. The significant shift from the neutral exciton at 1.84 eV (red spectra in the inset of Fig. 5c) to the highest located peak at 1.78 eV (blue spectra) is partially associated with this effect since it differs from results reported by Feuer et al. ¹⁰, the mentioned difference is likely related to various dielectric environments and/or strains. Upon encapsulation, the sample is protected from molecular physisorption and as a result, the contribution from different excitonic complexes, including bound exciton defect states, will be unaffected and more visible^{85,86}.

The broad nature of the defect-related emission shown in Fig. 5c is likely to be a convolution of multiple peaks attributed to various point defects shown in Fig. 2. The deconvoluted PL spectra fitted by Lorentzian functions show the presence of at least three distinct peaks at room temperature indicated by the labels P1, P2, and P3 (blue-shaded curves). The results of the fitting procedure regarding the energy of the P1, P2, and P3 emission peaks are in excellent agreement with our DFT calculations (Fig. 4) and are attributed to V_S , V_{Se} , and $V_S - V_{Se}$ at 1.68, 1.57, and 1.54 eV respectively at ambient temperatures and pressures. At cryogenic temperature (4 K), emission from bound exciton species dominates the optical emission from this device, and spectrally narrow emission peaks can be individually identified (See SI Fig. S6). Low-temperature power-dependence PL of these defect states revealed a saturation behaviour consistent with the nature of bound exciton emission in the TMDs ^{28,63}. Fig. 5f, 5g, and 5h show, respectively, the power-dependence data are fit to a saturation curve assuming two-level system, yielding fit values for the saturation powers below 1 uW for all three spectral lines. The PL saturation at low optical power and saturation behavior consistent with a two-level system indicates the presence of isolated defects within the detection volume.

Conclusions. Overall, electron microscopy and optical spectroscopy studies, together with DFT simulations, introduced and structurally characterized the most common type of 0D point and 1D line defects in 2D Janus TMDs monolayers and correlated them to their optical properties. Cryogenic excitonic studies show that most defect states (V_S , V_{Se} , and $V_S - V_{Se}$) are optically active and manifest themselves in various bound excitonic states. Comprehensive density functional theory studies offered thermodynamic insights into the structural properties of these imperfections and correlated their energetic states and photoexcited carrier relaxation processes to the observed emission characteristics. Overall, studies point out that even for the best-in-class Janus materials reported to date, a significant number of point defects exist, and more creative growth methods, such as atomic layer deposition or solution-based processing, are needed to further improve the quality of 2D Janus IMDs and established the first correlation between structural imperfections and material properties as a guideline for future studies, especially towards their

synthesis using and the development of electronic devices capitalizing on exotic/superior properties of these emergent semiconductors.

Methods:

CVD Synthesis: Monolayer Transition Metal Dichalcogenides (TMDs) were synthesized directly on SiO₂/Si substrates using established parameters from the literature^{15,17,28}. Initially, the substrates were meticulously cleaned using a piranha etchant, followed by double sonication in deionized water to eliminate any residual etchant, followed by further sonication in ethanol and isopropyl alcohol for five minutes and subjected to a 75 W oxygen plasma treatment for fifteen minutes. The synthesis was done in an Atmospheric Pressure Chemical Vapor Deposition (AP-CVD) system. This system comprises a one-inch inner diameter quartz tube within a single-zone tube furnace (Lindberg Blue/M). The tube was cleaned with soap and deionized water before use. Less than 50 mg of Tungsten (VI) Oxide (Sigma-Aldrich, ACS reagent, \geq 99.5%)) was distributed in a 7 ml Coors Tek combustion boat for TMDs synthesis. A 50 μ M Perylene-3,4,9,10-tetracarboxylic acid tetrapotassium salt (PTAS) solution was applied to one substrate to enhance nucleation. Selenium powder, used as the chalcogen source, was placed upstream relative to the gas flow, with a reaction zone temperature of approximately 300°C. The furnace was ramped up to 850 °C in sixteen minutes, maintaining an argon flow rate of 80 SCCM and introducing 4 SCCM of hydrogen at the peak temperature for five minutes. Post-synthesis, the furnace cooled naturally, with the hydrogen supply cut off, and argon flow increased to 200 SCCM. The reaction of MoSe₂ monolayers was carried similarly with Molybdenum (VI) Oxide (Sigma-Aldrich, ACS reagent, ≥99.5%) precursor, reaction temperature of 760 °C and a flow rate of 46 SCCM UHP Argon.

CVT Synthesis and exfoliations Bulk WSe2 crystals, synthesized via chemical vapour transport 15,33, briefly, Tungsten foil (Alfa Aesar, 99.999% metal basis) and selenium powder (Thermo Scientific, 200 mesh, 99.999%) were added to a quartz ampoule in stochiometric ratio by mole basis and heated to 1000 °C gradually in 72 hours to prepare a polycrystalline charge. Before growth, the transition metals were treated with dilute nitric acid to remove native oxides. The polycrystalline powder is pulverized in a ball mill for 24 hours and analyzed via Wavelength Dispersive Spectroscopy (WDS) to quantify the stoichiometry. This powdered WSe2, mixed with 90 mg Tellurium Tetrachloride(TeCl4) as a transport agent, is added to a quartz ampule that is cleaned with hydrofluoric acid (HF) to remove any organic residues. The ampoule is loaded in a three-zone furnace, with the precursors set at a hot zone at 1100°C and the growth zone at 1000°C on the other side of the ampoule. Single crystal WSe2 was obtained after 100 hours of growth and was exfoliated onto silicon substrates with a 300 nm thermal oxide layer. The exfoliation process involved multiple steps, initially utilizing Nitto Blue tape to achieve the desired sample thickness. Subsequently, this thinned sample was transferred to a polydimethylsiloxane (PDMS) layer to minimize tape residue. This PDMS stamp was carefully pressed against an ultra-clean silicon substrate, which had been previously treated with 75 W oxygen plasma. To further improve the contact between the substrate and the stamp, the PDMS silicon substrate was placed in a vacuum chamber for ten more minutes, eliminating air pockets. After removing the stamp, the sample was assessed by photoluminescence spectroscopy, explicitly looking for the absence of indirect emission to identify the regions of interest accurately.

In-Situ Selective Epitaxy and Replacement: The synthesis of 2D Janus TMDs is performed in a custombuilt glass reaction chamber consisting of two glass arms serving as the inlet and outlet manifold. Ultrapure hydrogen is introduced through the inlet, with the chamber's pressure regulated and monitored by a pressure gauge and capacitance manometer attached to the manifolds. CVD-grown and mechanically exfoliated TMD monolayers, used as reaction precursors, are placed at the centre of the synthesis chamber. Upstream to the gas flow, a secondary chalcogen source (sulphur) is positioned on a quartz stage. The chamber's outlet manifold is connected to a two-stage rotary vane pump (Edwards RV12), maintaining a pressure of 300 mTorr throughout the synthesis. Before synthesis, the chamber is evacuated of air and held under vacuum for fifteen minutes. Hydrogen at a flow rate of 20 SCCM is then introduced into the chamber and stabilized for ten minutes before commencing synthesis. Around the outlet manifold, a copper coil is connected to an RF generator (SEREN 101R) and an impedance-matching network (custom-designed). Hydrogen plasma is ignited by supplying 20 W of power to the coil. The synthesis process is conducted under a Raman Optical Spectrophotometer (Renishaw In-Via Confocal Raman Microscope) equipped with a 488 nm laser, focused using a long-distance objective (20x Infinity Corrected Mitutoyo Plan Apo SL). Raman spectroscopic data is collected to assess the optimal conversion of the TMDs into Janus monolayers (See Fig. 1a). Adjustments to power and flow rate are made throughout the conversion process based on the in-situ Raman data collected during the measurement.

h-BN Janus Heterostructure Fabrication: The h-BN Janus heterostructures were prepared by first exfoliating a few layers of h-BN onto a silicon substrate with a 300 nm thermally grown oxide layer. Before exfoliation, the substrates were cleaned using piranha solution and treated with plasma to eliminate organic residues. Subsequently, the substrate underwent annealing at 150 °C in an ultra-high vacuum (UHV) environment to enhance the adhesion of the h-BN to the SiO₂ substrate. This step was followed by a chloroform treatment to remove any polydimethylsiloxane (PDMS) residues. Next, a monolayer of WSe₂ was deterministically transferred onto the substrate using a PDMS stamp, a transfer station, and a set of micromanipulators. The substrate with the WSe₂ layer was then annealed again at 150 °C and cleaned with chloroform to improve contact and remove any remaining PDMS residue. The WSe₂ monolayer on h-BN was converted into Janus W^S_{Se} through the SEAR process, followed by encapsulation with an additional few layers of h-BN prepared on PDMS. The fully encapsulated structure underwent a final round of annealing and cleaning before being characterized by optical measurements.

Cryogenic Photoluminescence Spectroscopy: All measurements at 4 K are carried out in a closed-cycle cryostat (the AttoDRY1000 from Atto cube Systems AG). Excitation and light collection are facilitated through a custom-built confocal microscope operating in reflection geometry. This microscope has an apochromatic objective lens with a numerical aperture (NA) of 0.81 (model LT-APO/NIR/0.81, also from Atto cube Systems AG). For the photoluminescence (PL) measurements, continuous-wave excitation is employed using a 2.33 eV laser (Ventus 532, from Laser Quantum Ltd.). The excitation power dependence is measured on the sample, and the optical intensity is calculated based on the optical spot size, determined by the 0.81 NA of the objective lens.

Scanning Transmission Electron Microscopy and Sample Preparation: 2D Transition Metal Dichalcogenide (TMD) monolayers were exfoliated onto an SI substrate with 300 nm oxide layer and converted to Janus TMDs using SEAR, a solution of Poly(Bisphenol A Carbonate) (PC) in chloroform was spin-coated onto the substrate and dried, forming a uniform film. The TMDs/PC assembly was transferred then using adhesive thermal release tape (Nitto Denko REVALPHA, TRT). This assembly was carefully placed onto a Quantifoil holey carbon grid using micromanipulators. A glass slide was used to facilitate

handling and heating it to 90 °C, separating the TMDs/PC structure from the TRT. The PC film was dissolved in heated chloroform vapour, and the transferred monolayer was finally inspected under a microscope and through Raman spectroscopy to confirm the absence of chloroform residue.

The HAADF STEM images were collected on a Nion Hermes Ultra STEM 100 microscope operated at 100 keV acceleration voltage, the probe convergence angle was set to 33 mrad, a beam current on the detector was about 25 pA, and an inner collection semi-angle of 80 mrad on the annular detector. Before the measurement, the sample was baked at 160 °C for 16 hours to reduce contamination during the experiment. The images were filtered and denoised by deconvolution of the point spread function (PSF) of the electron beam from the raw image by the Richardson-Lucy deconvolution algorithm.

First-Principles Computations: Defect computations were performed using Vienna Ab-initio Simulation Package (VASP)^{87,88} and the projector-augmented wave (PAW) method⁸⁹ with the global hybrid functional PBE0^{90,91}. A 144-atom orthorhombic monolayer supercell simulated each charged defect within a 24 Å vacuum layer. The plane-wave basis cutoff energy was set to 400 eV, and only the Γ point was used to sample the Brillouin zone. The defect structures were optimized at a fixed volume until the force on each ion was less than 0.01 eV/Å. The defect formation energy for each charged defect was computed using PyCDT. For a general defect X at charge state q, its formation energy $E_{form}[X^q]$ is given by:

$$E_{form}[X^q] = E_{tot}[X^q] - E_{tot}^{bulk} - \sum n_i \mu_i + qE_F + E_{corr},$$

where $E_{form}[X^q]$ and $E_{tot}[X^q]$ are the total energies of the supercell containing the defect and the pristine one, respectively. The third term accounts for the energy needed to exchange atoms with the chemical reservoirs when creating the defect, where n_i specifies the number of atoms with species *i* being added $(n_i > 0)$ or removed $(n_i < 0)$ with corresponding chemical potential μ_i . The fourth term accounts for the electron exchange with the host material given by the Fermi level E_F , which is commonly referenced as the valence band maximum (VBM). The last term contains corrections for the finite-size effects, and we employ the methods from Komsa et al.^{92,93} as implemented in the SLABCC⁹⁴. The chemical potential of each atom is set to that of its elemental form. The band-edge position for WS₂ was computed in a primitive monolayer cell with a 12x12x12 k-point mesh, and a 22% Fock exchange was used for an improved description of the bandgap. Defect levels (red solid lines) are computed using 7% PBE0 functionals to fulfill the generalized Koopman's condition as detailed in our previous work ⁷⁷. Spin-orbit coupling is considered throughout the electronic-structure calculations unless otherwise specified. The single-particle Kohn-Sham level correction includes the charge corrections and the vacuum level alignment.

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The Defects Genome of Janus Transition Metal Dichalcogenides

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Figure S1: Simulated HAADF in 1L WSe₂ and Janus W_{Se}^{S} – (a) Experimental HAADF micrograph and (b) simulated HAADF micrograph of 1L- WSe₂ similarly, (c) shows the Experimental HAADF micrograph of 1L-Janus W_{Se}^{S} and (d) shows its simulated HAADF micrograph.



Figure S2: Simulated HAADF micrographs of defect configurations in 1L Janus W_{Se}^{S} - (a) single sulfur vacancy V_{S} , (b) single selenium vacancy V_{Se} , (c) sulfur-selenium vacancy V_{S} - V_{Se} ,



Figure S3: Simulated defect configurations in 1L Janus W_{Se}^{S} – (a) single sulfur vacancy V_{S} , (b) single selenium vacancy V_{Se} , (c) single tungsten vacancy V_{W} , (d) sulfur-selenium vacancy $V_{S-}V_{Se}$, and (e) sulfur-selenium-tungsten vacancy $V_{S-}V_{Se} - V_{W}$.



Figure S4: Defect formation energy diagram in 1L Janus W_{Se}^{S} – formation energy diagram for selected simple and complex defects at charge state –1, 0 and +1. Dashed lines indicate the competition between forming complex defects and simple defects.



Figure S5: Kohn-Sham energy level diagrams for neutral V_S , V_{Se} and $V_S - V_{Se}$. (a) Without SOC, the ground state is a singlet with 4 degenerate states within the bandgap. Here only one spin channel is shown for simplicity. (b) SOC splits the degenerate state by 210 meV, 214 meV and 293 meV for neutral V_S , V_{Se} and $V_S - V_{Se}$, respectively.



Figure S6:Cryogenic PL Spectra in 1L Janus W_{Se}^s device shown in Fig. 51 – (a) PL spectra obtained from four random spots at 1.72 eV attributed to single sulfur vacancies V_S, similarly (b) shows the PL emission from four random spots at 1.65 eV attributed to single selenium vacancy V_{Se}, (c) shows PL spectra obtained at 1.60 eV attributed to sulfur-selenium vacancy V_S–V_{Se}, from four random spots: All spectra were processed and analysed via a MATLAB script, with specified wavelength limits as a guide for peak search algorithm. The algorithm implements a Lorentzian profile fitting to identify the relevant peaks and extract critical parameters, ensuring precise spectral characterization (d) Shows the distribution of the FWHM for peak at 1.72 eV for twelve random PL spectra. Similarly (e) and (f) show the distribution of FWHM for the peaks at 1.65 eV and 1.60 eV respectively.